



BRAINWARE UNIVERSITY

Term End Examination 2023-2024

Programme – B.Tech.(CSE)-2023

Course Name – Basic Electrical and Electronics Engineering

Course Code - ESCG201

(Semester II)

Full Marks : 60

Time : 2:30 Hours

[The figure in the margin indicates full marks. Candidates are required to give their answers in their own words as far as practicable.]

Group-A

(Multiple Choice Type Question)

1 x 15=15

1. Choose the correct alternative from the following :

- (i) Identify the unit of frequency is
- | | |
|-----------------|-----------------|
| a) Cycle | b) Cycle-second |
| c) Hertz/second | d) Hertz |
- (ii) Calculate the peak value of a sine wave if r.m.s value is 100 A
- | | |
|----------|-----------|
| a) 70.7A | b) 141A |
| c) 150A | d) 282.8A |
- (iii) Determine the identity of a pure inductive circuit
- | | |
|---------------------------|---------------------------|
| a) Actual power is zero | b) Reactive power is zero |
| c) Apparent power is zero | d) None of the above |
- (iv) Indicate the correct option of the fixed losses in a transformer
- | | |
|----------------------|--|
| a) Eddy current loss | b) Hysteresis loss |
| c) Copper loss | d) Both Eddy current and hysteresis losses |
- (v) Choose from the following, the correct option, according to Kirchoff's voltage law
- | | |
|--|---|
| a) The algebraic sum of all the e.m.f's in the circuit is zero | b) Algebraic sum all the voltage drops in the circuit is zero |
| c) Algebraic sum of e.m.f's plus algebraic sum of voltage drops is equal to zero | d) All of these |
- (vi) Identify the relation between the line voltage and the phase voltage in case of three phase star connection
- | | |
|---|---------------------------------------|
| a) line voltage = 1.732 x phase voltage | b) line voltage = phase voltage |
| c) phase voltage = 1.732 x line voltage | d) phase voltage = 0.5 x line voltage |
- (vii) Calculate the rectification efficiency of a half-wave rectifier using applied input a.c. power is 100 watts and the d.c. output power obtained is 40 watts.
- | | |
|--------|---------|
| a) 20% | b) 40% |
| c) 60% | d) 100% |

- (viii) Select the reverse saturation current in junction diode is independent of
- | | |
|--------------------------------------|------------------|
| a) Potential barrier | b) Junction area |
| c) Doping of 'P' and 'N' type region | d) Temperature |
- (ix) Select the positive terminal of the battery is connected to the anode of the diode, then it is known as
- | | |
|-------------------|---------------------|
| a) Forward biased | b) Reverse biased |
| c) Equilibrium | d) Schottky barrier |
- (x) Choose when a forward biased is applied to a diode, the electrons enter to which region of the diode
- | | |
|-----------------|---------------|
| a) P-region | b) N-region |
| c) P-n junction | d) Metal side |
- (xi) Identify during reverse bias, a small current develops which is known as
- | | |
|-------------------------------|--------------------|
| a) Forward current | b) Reverse current |
| c) Reverse saturation current | d) Active current |
- (xii) Indicate the Fermi level of an n-type semiconductor lies
- | | |
|---------------------------------------|-------------------------------|
| a) near the conduction band-edge | b) near the valence band edge |
| c) at the middle of the forbidden gap | d) near the valence band-edge |
- (xiii) Indicate the band gaps of silicon and germanium are
- | | |
|-----------------------|--------------------------|
| a) 0.67 eV and 1.1 eV | b) 0.87 eV and 6.78 eV |
| c) 5.89 eV and 4.6 eV | d) 0.54 eV and 0.7861 eV |
- (xiv) Indicate that the electron hole pairs are generated by
- | | |
|------------------|----------------------|
| a) ionisation | b) thermal agitation |
| c) recombination | d) doping |
- (xv) Choose that at 0 K an intrinsic semiconductor behaves as a/an
- | | |
|------------------|---------------------|
| a) Conductor | b) Insulator |
| c) Semiconductor | d) Any of the above |

Group-B

(Short Answer Type Questions)

3 x 5=15

2. Explain why only low voltage is applied to the transformer during short circuit test. (3)
3. State Norton's theorem. (3)
4. Explain the phenomenon of diffusion of current carriers in a semiconductor. (3)
5. Illustrate short note about Avalanche Breakdown. (3)
6. Differentiate among Active region, Cut-off region and Saturation region at CB mode. (3)

OR

- Deduce the relation between β and α . (3)

Group-C

(Long Answer Type Questions)

5 x 6=30

7. Explain the power factor and apparent power. (5)
8. Comparison between CB, CE and CC configuration of Transistor. (5)
9. In a common base connection, $\alpha = 0.95$. The voltage drop across $2\text{ k}\Omega$ resistance which is connected in the collector is 2 V . Find the base current. (5)
10. Distinguish between intrinsic and extrinsic semiconductors and explain the term "Doping". (5)
11. Explain the Drift current and Diffusion current in a semiconductor device? (5)
12. A 4 pole 220 V dc shunt motor has armature and shunt field resistance of 0.2 ohm and 220 ohm respectively. It takes 20 A at 220 v from the source while running at a speed of 1000 rpm . Calculate field current, armature current, and back emf. (5)
- OR**
- Explain the Armature control method in DC motors. (5)
